

Please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please amend the Claims as follows:

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16 - 24 (Withdrawn)

25. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate;
an interlayer insulating film located on the semiconductor substrate;
wirings located on the interlayer insulating film; and
a passivation film covering the surface top surfaces of the interlayer insulating
film and the wirings, including a first insulating film that is a modified Spin-on-Glass
(SOG) film of an organic SOG film, wherein the modified SOG film contains containing
boron impurity and being in condition where organic component is decomposed.

26. (Previously Added) The semiconductor device according to Claim 25,
wherein the passivation film includes a second insulating film, located on at least one of
an upper side and a lower side of the first insulating film, having a hygroscopicity lower
than that of the first insulating film.

27. (Previously Added) The semiconductor device according to Claim 26,
wherein the second insulating film is selected from the group consisting of silicon nitride
film, silicon oxide film and silicon oxynitride film.

28. (Currently Amended) The semiconductor device according to Claim 25,
wherein the first insulating film contains the boron impurity to decompose organic
components of the an organic SOG film.

29. (Previously Added) The semiconductor device according to Claim 28,
wherein the passivation film includes a second insulating film, located on at least one of

an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

30. (Previously Added) The semiconductor device according to Claim 29, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

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31. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate;
an interlayer insulating film located on the semiconductor substrate;
wirings located on the interlayer insulating film; and

5 a passivation film covering the surface top surfaces of the interlayer insulating film and the wirings, including a first insulating film that is a modified Spin-on-Glass (SOG) film of an inorganic SOG film, wherein the modified SOG film contains containing boron impurity and inorganic component.

32. (Previously Added) The semiconductor device according to Claim 31, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

33. (Previously Added) The semiconductor device according to Claim 32, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.